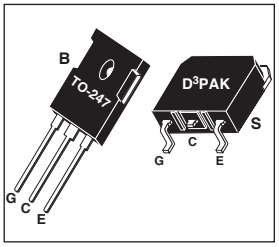
ADVANCED POWER TECHNOLOGY®

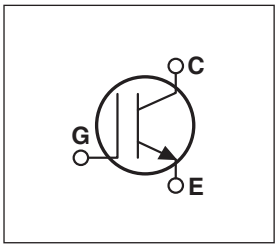
1200V

APT13GP120B APT13GP120S
APT13GP120BG* APT13GP120SG*

***G Denotes RoHS Compliant, Pb Free Terminal Finish.**

POWER MOS 7® IGBT





The POWER MOS 7® IGBT is a new generation of high voltage power IGBTs. Using Punch Through Technology this IGBT is ideal for many high frequency, high voltage switching applications and has been optimized for high frequency switchmode power supplies.

- **Low Conduction Loss**
- **Low Gate Charge**
- **Ultrafast Tail Current shutoff**
- **100 kHz operation @ 600V, 10A**
- **50 kHz operation @ 600V, 16A**
- **RBSOA Rated**

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT13GP120B_S(G)	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	±30	
I_{C1}	Continuous Collector Current @ T_C = 25°C	41	Amps
I_{C2}	Continuous Collector Current @ T_C = 110°C	20	
I_{CM}	Pulsed Collector Current ①	50	
RBSOA	Reverse Bias Safe Operating Area @ T_J = 150°C	50A @ 960V	
P_D	Total Power Dissipation	250	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 500µA)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 1mA, T_j = 25°C)	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 13A, T_j = 25°C)		3.3	3.9	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 13A, T_j = 125°C)		3.0		
I_{CES}	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 25°C) ②			500	µA
	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 125°C) ②			3000	
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V)			±100	nA

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - http://www.advancedpower.com

050-7412 Rev E 1-2006

DYNAMIC CHARACTERISTICS

APT13GP120B_S(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	**Capacitance**		1145		pF
C_{oes}	Output Capacitance	V_{GE} = 0V, V_{CE} = 25V		90		
C_{res}	Reverse Transfer Capacitance	f = 1 MHz		15		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge		7.5		V
Q_g	Total Gate Charge ③	V_{GE} = 15V		55		nC
Q_{ge}	Gate-Emitter Charge	V_{CE} = 600V		8		
Q_{gc}	Gate-Collector ("Miller") Charge	I_C = 13A		26		
RBSOA	Reverse Bias Safe Operating Area	T_J = 150°C, R_G = 5Ω, V_{GE} = 15V, L = 100µH, V_{CE} = 960V	50			A
$t_{d(on)}$	Turn-on Delay Time	**Inductive Switching (25°C)**		9		ns
t_r	Current Rise Time	V_{CC} = 600V		12		
$t_{d(off)}$	Turn-off Delay Time	V_{GE} = 15V		28		
t_f	Current Fall Time	I_C = 13A		34		
E_{on1}	Turn-on Switching Energy ④	R_G = 5Ω		115		µJ
E_{on2}	Turn-on Switching Energy (Diode) ⑤	T_J = +25°C		330		
E_{off}	Turn-off Switching Energy ⑥			165		
$t_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)**		9		ns
t_r	Current Rise Time	V_{CC} = 600V		12		
$t_{d(off)}$	Turn-off Delay Time	V_{GE} = 15V		70		
t_f	Current Fall Time	I_C = 13A		200		
E_{on1}	Turn-on Switching Energy ④	R_G = 5Ω		225		µJ
E_{on2}	Turn-on Switching Energy (Diode) ⑤	T_J = +125°C		710		
E_{off}	Turn-off Switching Energy ⑥			840		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case **(IGBT)**			.50	°C/W
$R_{\theta JC}$	Junction to Case **(DIODE)**			N/A	
W_T	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

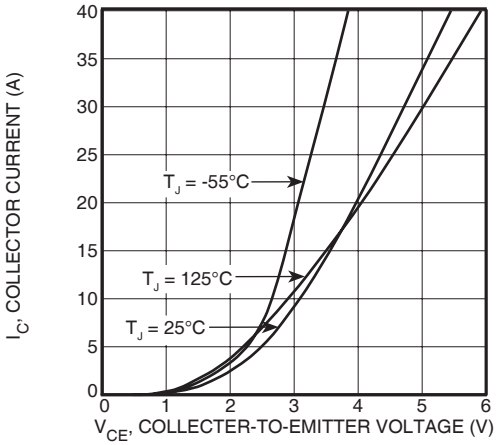


FIGURE 1, Output Characteristics(T_J = 25°C)

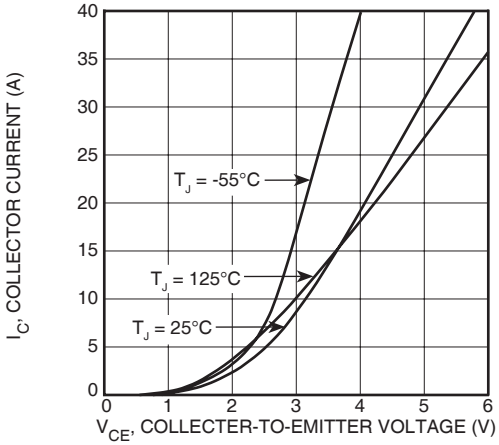


FIGURE 2, Output Characteristics (T_J = 125°C)

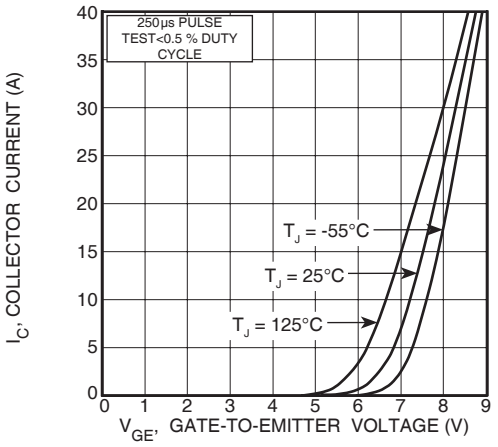


FIGURE 3, Transfer Characteristics

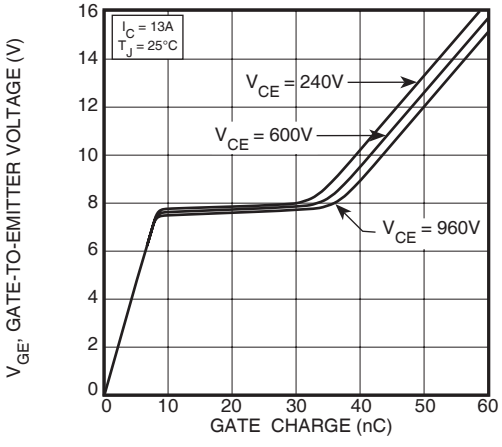


FIGURE 4, Gate Charge

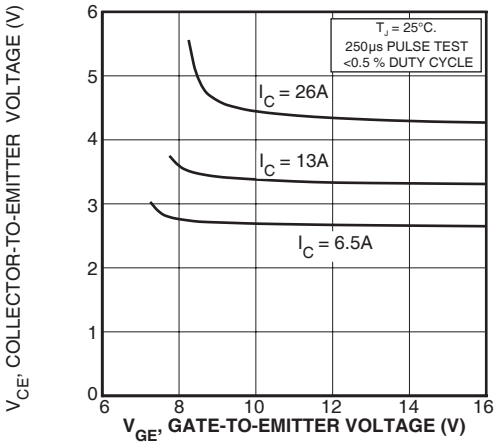


FIGURE 5, On State Voltage vs Gate-to- Emitter Voltage

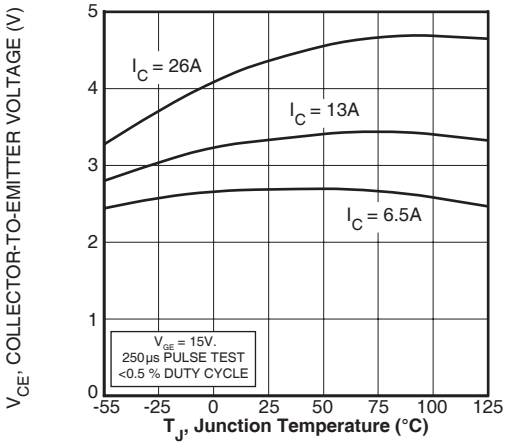


FIGURE 6, On State Voltage vs Junction Temperature

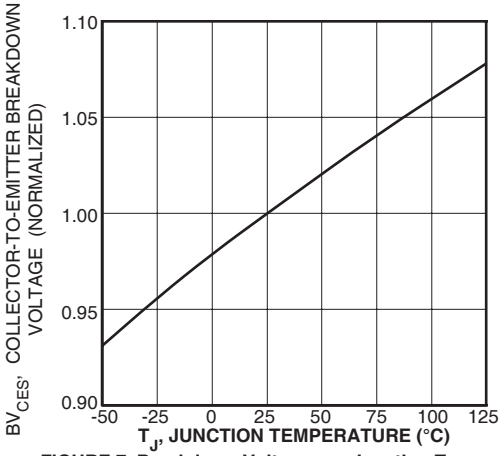


FIGURE 7, Breakdown Voltage vs. Junction Temperature

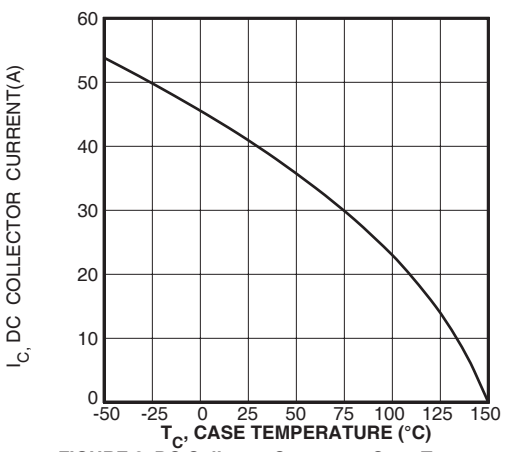


FIGURE 8, DC Collector Current vs Case Temperature

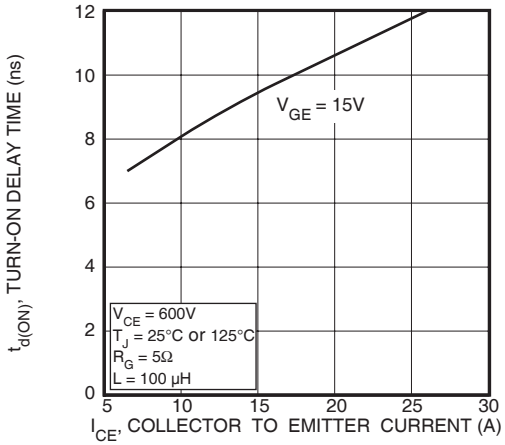


FIGURE 9, Turn-On Delay Time vs Collector Current

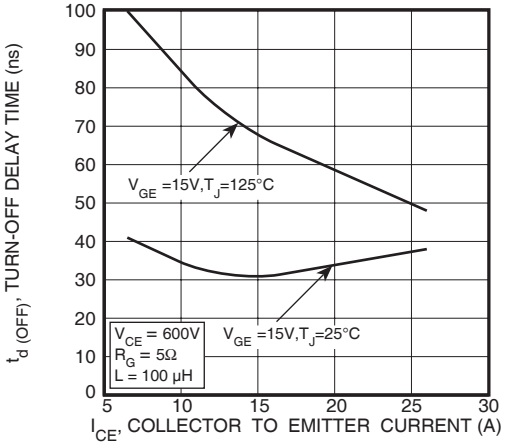


FIGURE 10, Turn-Off Delay Time vs Collector Current

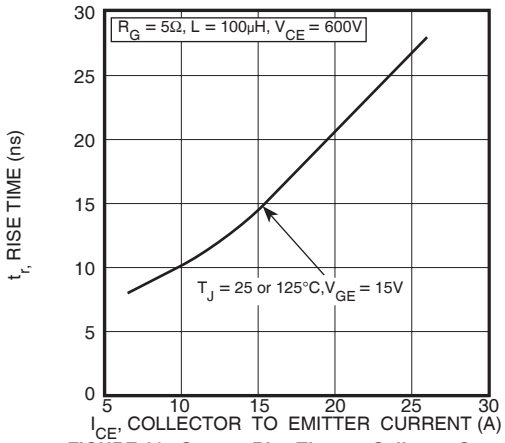


FIGURE 11, Current Rise Time vs Collector Current

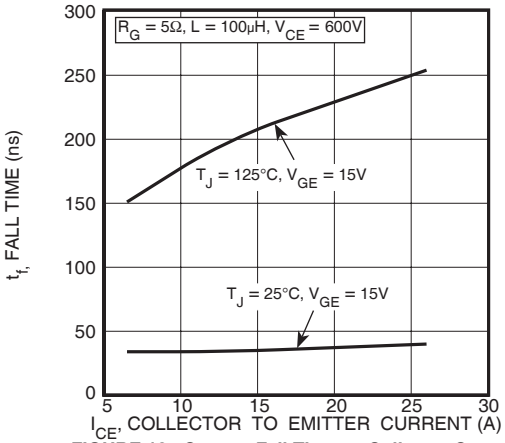


FIGURE 12, Current Fall Time vs Collector Current

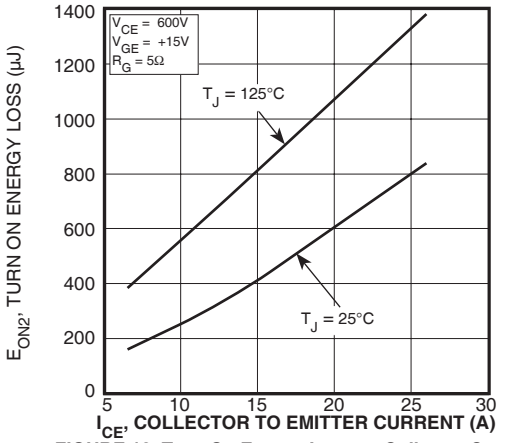


FIGURE 13, Turn-On Energy Loss vs Collector Current

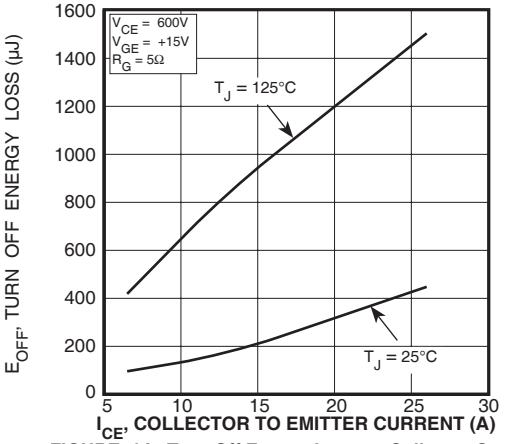


FIGURE 14, Turn Off Energy Loss vs Collector Current

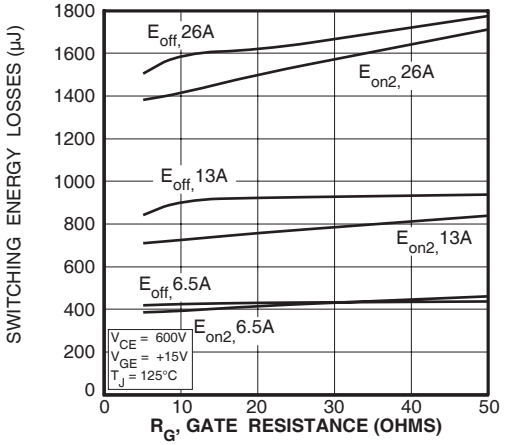


FIGURE 15, Switching Energy Losses vs. Gate Resistance

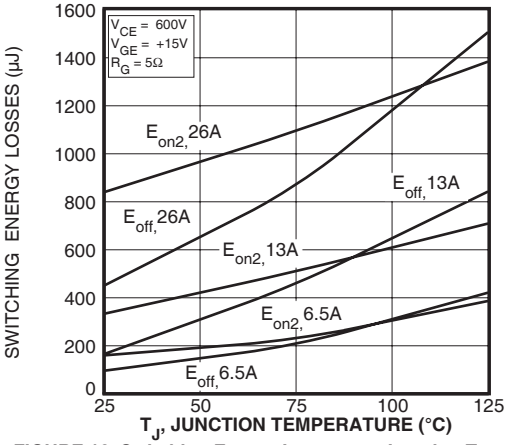


FIGURE 16, Switching Energy Losses vs Junction Temperature

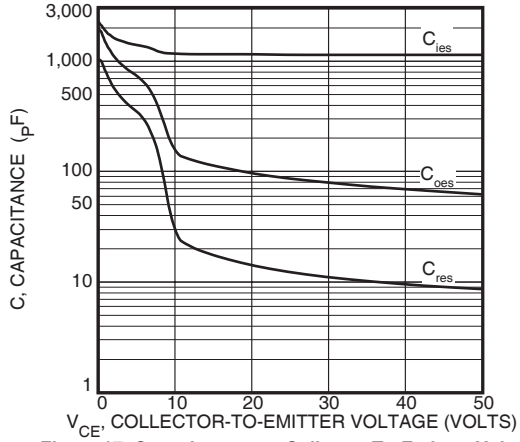


Figure 17, Capacitance vs Collector-To-Emitter Voltage

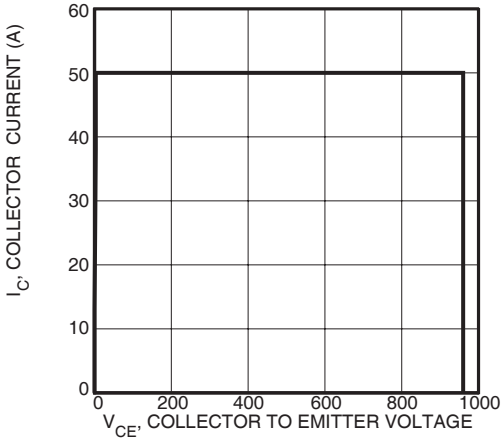


Figure 18,Minimim Switching Safe Operating Area

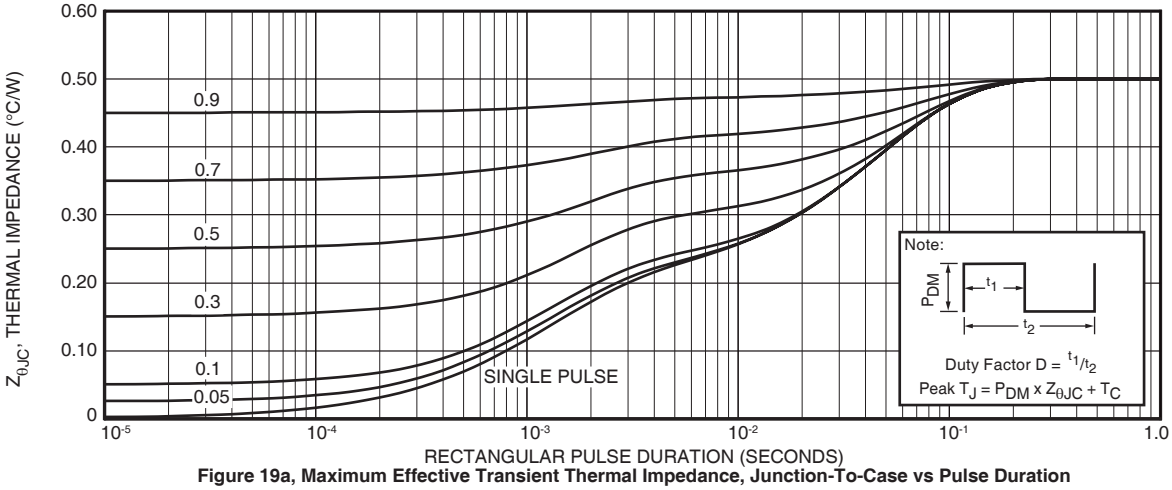


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

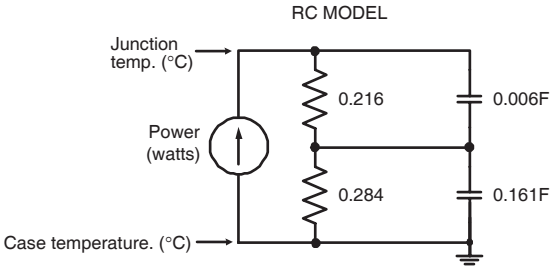


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

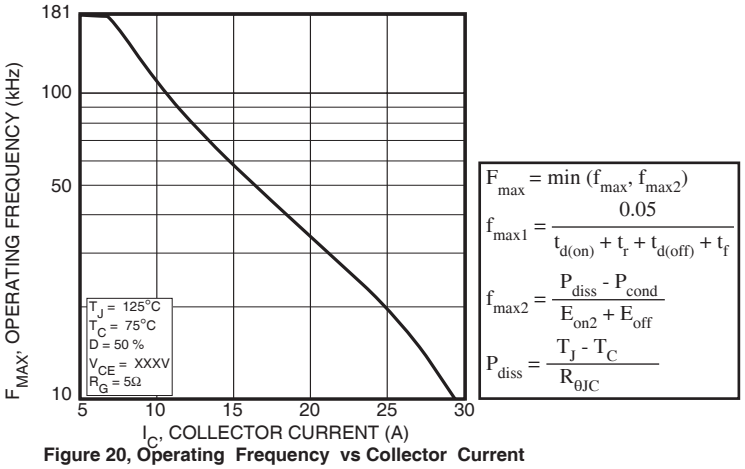


Figure 20, Operating Frequency vs Collector Current